

FIG.1A

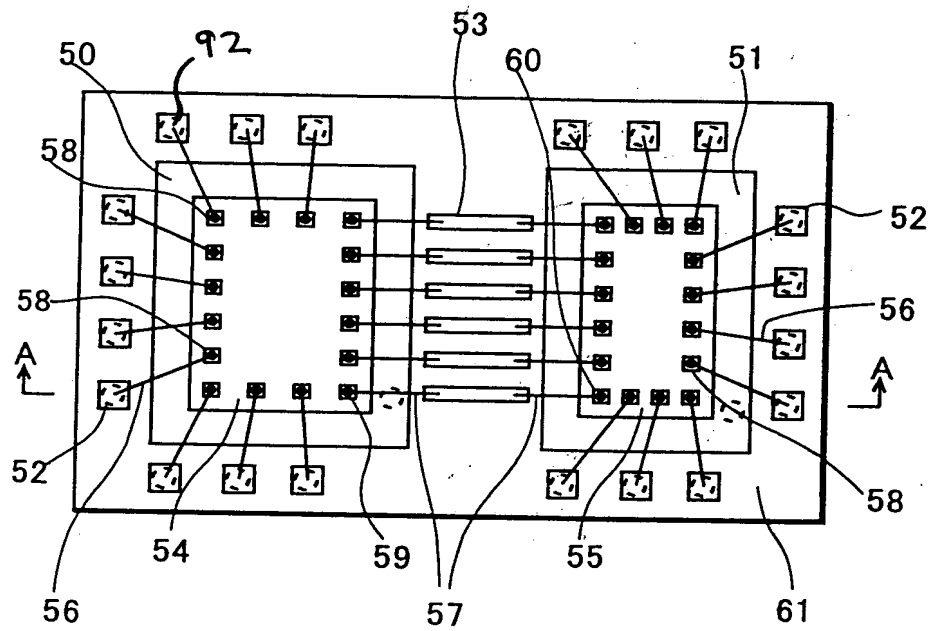


FIG.1B

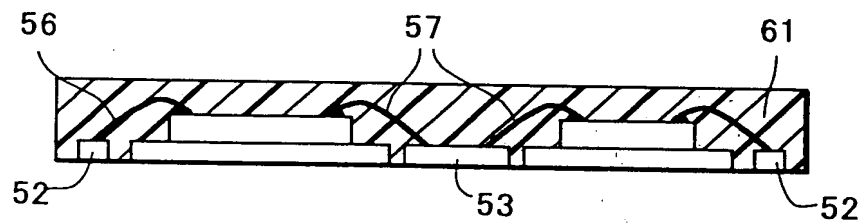


FIG.2A

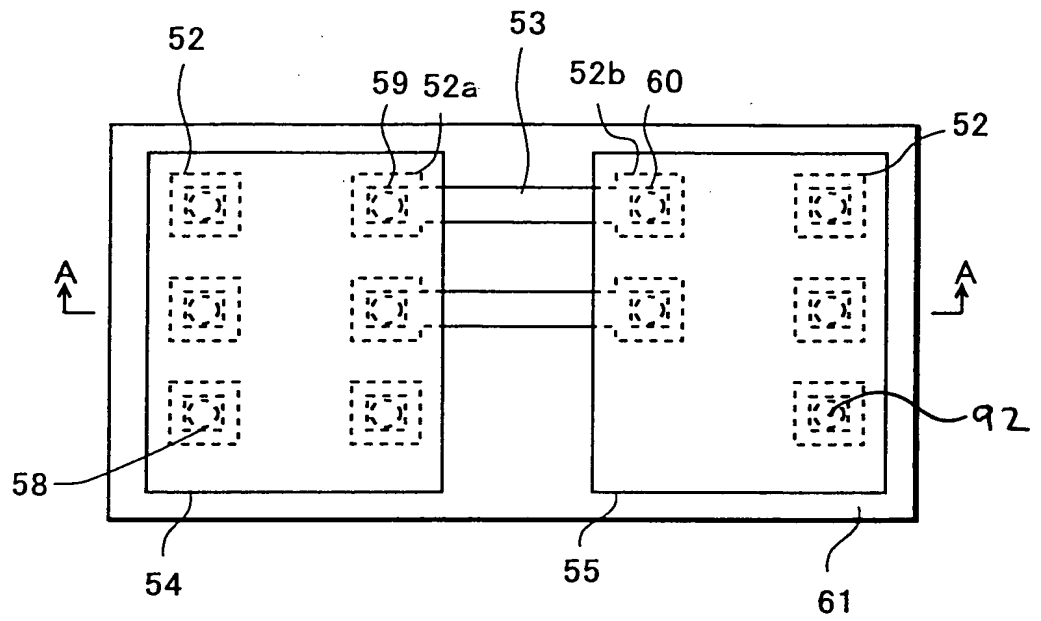


FIG.2B

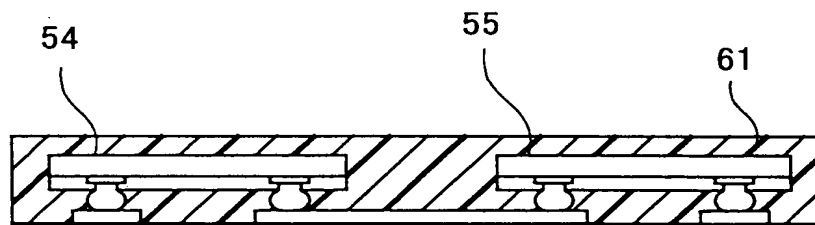


FIG.3A

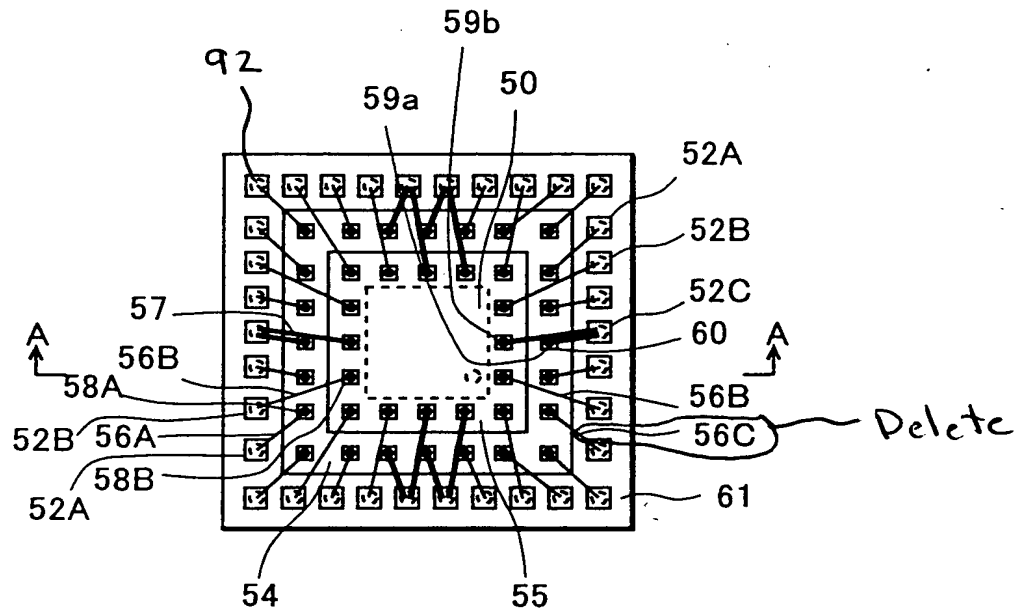
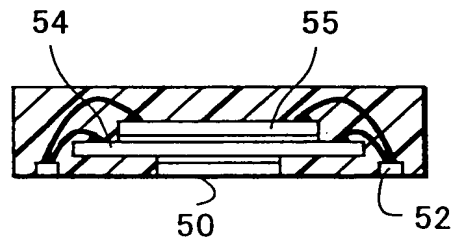


FIG.3B



[illegible]

A cross-sectional view of a semiconductor device. It shows a substrate with a patterned layer on top. The patterned layer has two main regions, each with a central rectangular block and two side rectangular blocks. A conductive layer is formed on top of the patterned layer, with a label 61 pointing to it.

FIG.5

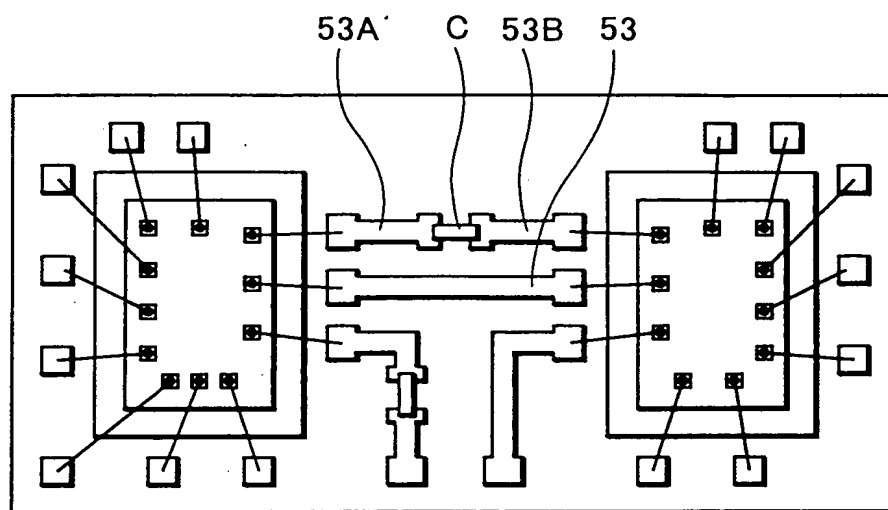
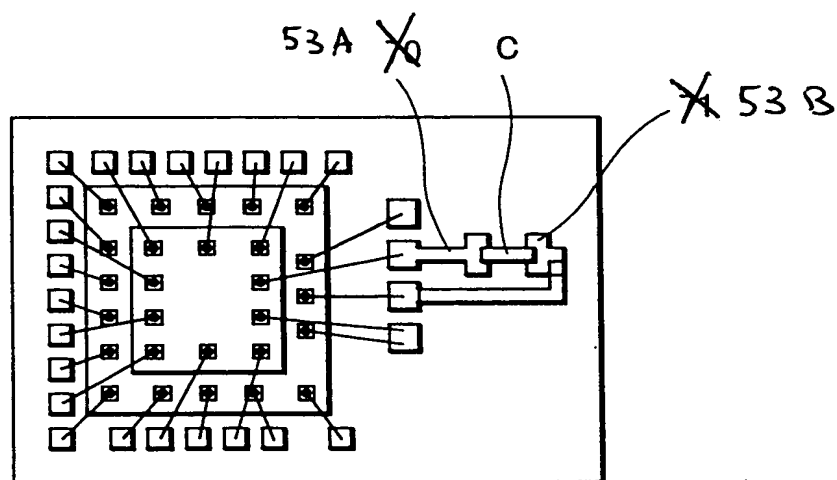


FIG.6



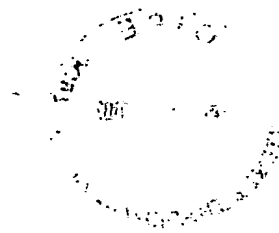


FIG.7

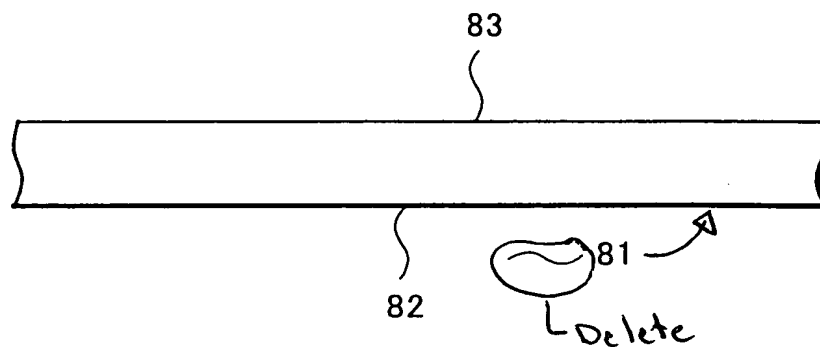


FIG.8

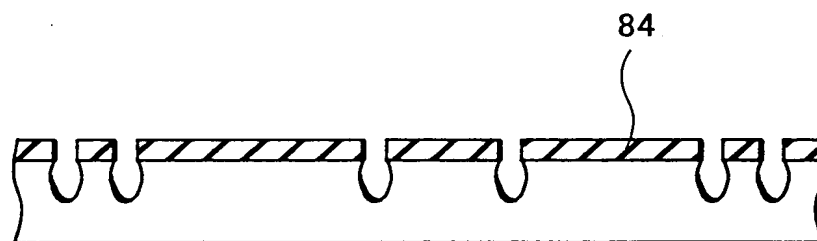


FIG.9

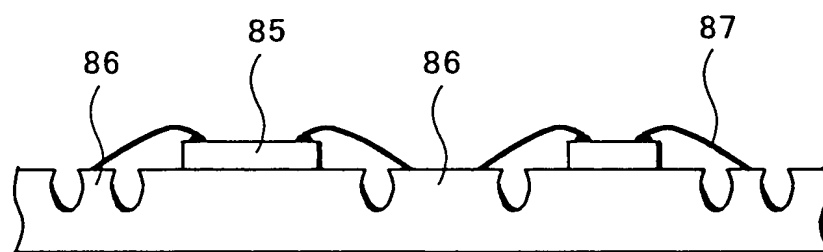


FIG.10

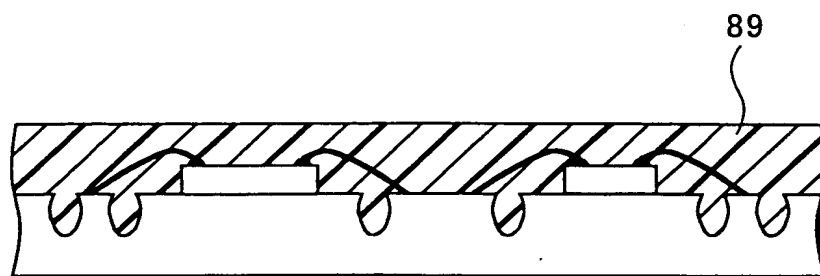


FIG.11

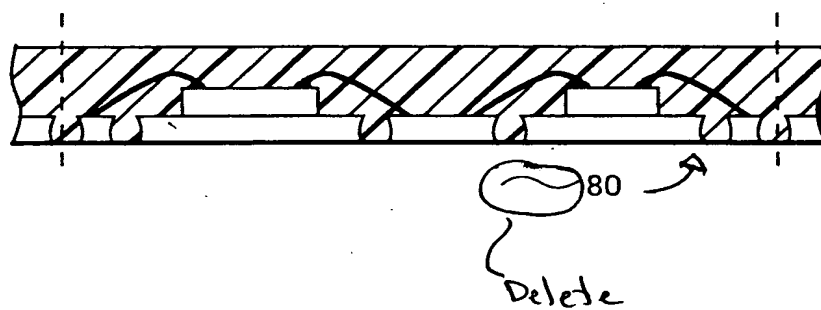


FIG.12 (Prior Art)

